

isc P-Channel Mosfet Transistor

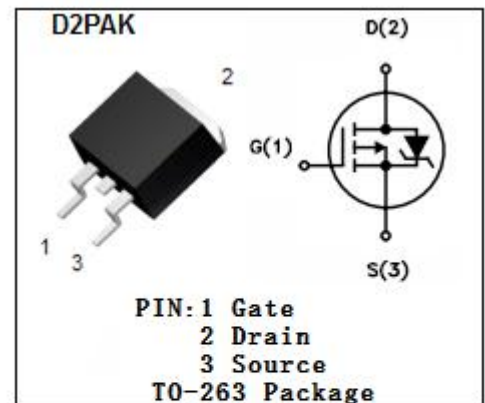
IRF9530S

FEATURES

- -12A, -100V
- Single pulse avalanche energy rated
- Static Drain-Source On-Resistance: $R_{DS(on)} = 0.3 \Omega$ (Max)
- SOA is power dissipation limited
- Nanosecond switching speeds
- Linear transfer characteristics
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

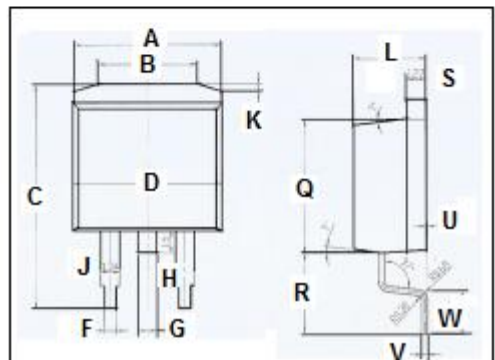
DESCRIPTION

- The power MOSFET is designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers and drivers for high power bipolar switching transistors requiring high speed and low gate drive power



• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^\circ\text{C}$	-12	A
I_{DM}	Drain Current-Single Pulsed	-48	A
P_{tot}	Total Dissipation@ $TC=25^\circ\text{C}$	75	W
T_j	Max. Operating Junction Temperature	-55~150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.67	$^\circ\text{C}/\text{W}$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ\text{C}/\text{W}$

isc P-Channel Mosfet Transistor
IRF9530S
ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D =-0.25mA	-100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =-0.25mA	-2.0		-4.0	V
V _{SD}	Diode Forward On-voltage	I _S = -12A; V _{GS} = 0			-1.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = -10V; I _D = -6.5A			0.3	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-100V; V _{GS} = 0			-25	μA
G _{fs}	Forward Transconductance	I _D =-6.5A	2			S
t _{d(on)}	Turn-on Delay Time	I _D =-12A; V _{DD} =50V; R _G =50 Ω; V _{GS} =10V			60	ns
t _r	Rise Time				140	
t _{d(off)}	Turn-off Delay Time				140	
t _f	Fall Time				140	

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.